

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Cancelled)

(2) (Currently Amended) A mask comprising:
a circuit pattern to be transferred to a substrate via an optical system; and
an inspection pattern to be used for a measurement of a line width of a pattern

B¹ transferred to said substrate,

wherein said inspection pattern includes:

a first measurement pattern;

a second measurement pattern to be superimposed on an image of said first measurement pattern; and

an extraction pattern to be superimposed on an image of said first measurement pattern and an image of said second measurement pattern, and to be used for an extraction of a predetermined image from a superimposed image of said first measurement pattern and said second measurement pattern.

3. (Original) A mask according to claim 2, wherein each of said first measurement pattern and said second measurement pattern comprises a plurality of linear patterns which are parallel to each other, and said extraction pattern has a shape which can extract at least one approximate rhombic shape image from an image to be formed by superimposing said first measurement pattern and said second measurement pattern intersecting at a predetermined angle. - claim -

4. (Previously Amended) A mask according to claim 2, wherein said inspection pattern is formed in a separate area to a circuit pattern area in which said circuit pattern is formed.

5. (Previously Amended) A mask according to claim 2, wherein said inspection pattern is a part of said circuit pattern.

6. (Previously Amended) A mask according to claim 2, wherein a line width of said inspection pattern corresponds to a line width of said circuit pattern.

B¹ 7. (Currently Amended) An exposure method comprising:
 an exposure step of transferring a circuit pattern of said mask of claim 2 onto a photosensitive substrate via an optical system; and
 a measurement step of measuring prior to said exposure step, using ~~an~~ said inspection pattern which is formed on said mask to be used in said exposure step, a line width of a pattern to be transferred to said substrate.

8. (Original) An exposure method according to claim 7, wherein exposure conditions of said substrate are adjusted based on said line width of said pattern measured in said measurement step.

9-10. (Cancelled)

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 11. (Currently Amended) A mask comprising:
 a base member;
 a first ~~linear-line-and-space~~ pattern formed on said base member ~~and which~~
~~has~~ with a predetermined line width; and
 a second ~~linear-line-and-space~~ pattern which is to be superimposed on an image of said first ~~linear-line-and-space~~ pattern and ~~has which is formed at a predetermined~~
angle with respect to said first line-and-space pattern with a line width different from that of
~~said first linear pattern~~ said predetermined line width.

12. (Currently Amended) A mask according to claim 11, wherein ~~said a~~ circuit pattern is formed in an area different from an area in which said first ~~linear-line-and-space~~ pattern and said second ~~linear-line-and-space~~ pattern are formed.

13. (Currently Amended) An exposure method comprising:

an exposure step of transferring a the circuit pattern of said mask of claim 12 onto a substrate via an optical system; and

a measurement step of measuring prior to said exposure step, using said first ~~linear-line-and-space~~ pattern and said second ~~linear-line-and-space~~ pattern which are formed on said mask used in said exposure step, a line width of a pattern to be transferred to said substrate.

B¹ 14. (Currently Amended) A method of manufacturing semiconductor devices comprising:

an exposure step of transferring a the circuit pattern of said mask of claim 12 onto a substrate via an optical system; and

a measurement step of measuring prior to said exposure step, using said first ~~linear-line-and-space~~ pattern and said second ~~linear-line-and-space~~ pattern which are formed on said mask to be used in said exposure step, a line width of a pattern to be transferred to said substrate.

15. (Previously Added) A mask according to claim 2, wherein said inspection pattern is an isolated pattern.

16. (Previously Added) A mask according to claim 2, wherein said inspection pattern is a line-and-space pattern.

17. (Currently Amended) A mask comprising:
a base member;
~~a circuit pattern formed on said base member; and~~ a first measurement pattern formed on said base member;
a second measurement pattern formed on said base member and to be superimposed on an image of said first measurement pattern; and
~~an inspection-extraction pattern formed on said base member; wherein said inspection pattern is formed in a separate area to a circuit pattern area in which said circuit~~

pattern is formed and to be superimposed on an image of said first measurement pattern and an image of said second measurement pattern, and to be used for extraction of a predetermined image from a superimposed image of said first measurement pattern and said second measurement pattern.

18. (Currently Amended) A mask according to claim 17, wherein a line width of said ~~inspection pattern~~ first measurement pattern and said second measurement pattern corresponds to a line width of ~~said a~~ circuit pattern.

19. (Currently Amended) A mask according to claim 17, wherein said ~~inspection~~ first measurement pattern and said second measurement pattern is an are isolated ~~pattern~~ patterns.

20. (Currently Amended) A mask according to claim 17, wherein said ~~inspection~~ first measurement pattern and said second measurement pattern each is a line-and-space pattern.

21. (Currently Amended) A mask according to claim 17, wherein ~~said inspection pattern comprises a first linear pattern formed with a predetermined line width, and a second linear pattern superimposed on an image of said first linear pattern and formed with a line width different from that of said first linear pattern~~ a line width of said first measurement pattern is different from a line width of said second measurement pattern.

22. (Currently Amended) An exposure method comprising:
an exposure step of transferring a circuit pattern of a said mask according to claim 17 onto a photosensitive substrate via an optical system; and
_____ a measuring step of measuring prior to said exposure, using the ~~inspection~~ extraction pattern which is formed on said mask to be used in said exposure step, a line width of a pattern to be transferred onto said substrate.

23. (New) A mask according to claim 11, further comprising an extraction pattern to be used for an extraction of a plurality of diamond-shaped images from a superimposed image of said first line-and-space pattern and said second line-and-space pattern.

B2 24. (New) A mask according to claim 17, wherein said extraction pattern is used to extract a diamond-shaped image from a superimposed image of said first measurement pattern and said second measurement pattern.
